

Tunneling electroresistance in ferroelectric tunnel junctions

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Atomistic Screening Mechanism of Ferroelectric Surfaces: An In Situ Study of the Polar Phase in Ultrathin BaTiO ₃ Films Exposed to H ₂ O. Nano Letters, 2009, 9, 3720-3725.	9.1	73
2	Effect of spin-dependent screening on tunneling electroresistance and tunneling magnetoresistance in multiferroic tunnel junctions. Physical Review B, 2010, 81, .	3.2	85
3	Sixteen resistive states of a tunnel junction with a composite barrier. EPJ Applied Physics, 2010, 51, 10604.	0.7	6
4	Strong influence of complex band structure on tunneling electroresistance: A combined model and <i>ab initio</i> study. Physical Review B, 2010, 82, .	3.2	22
5	Ferroelectric dead layer driven by a polar interface. Physical Review B, 2010, 82, .	3.2	51
6	The converse piezoelectric effect on electron tunnelling across a junction with a ferroelectric-ferromagnetic composite barrier. Journal Physics D: Applied Physics, 2010, 43, 135003.	2.8	5
7	Nanoscale Switching Characteristics of Nearly Tetragonal BiFeO ₃ Thin Films. Nano Letters, 2010, 10, 2555-2561.	9.1	149
8	Effects of electrodes and space charges on the tunneling electroresistance in the ferroelectric tunnel junction with a SrTiO ₃ /BaTiO ₃ composite barrier. Applied Physics Letters, 2010, 96, .	3.3	19
9	Multi-ferroic and magnetoelectric materials and interfaces. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2011, 369, 3069-3097.	3.4	190
10	Reversible and Reproducible Giant Universal Electroresistance Effect. Chinese Physics Letters, 2011, 28, 107308.	3.3	9
11	Influence of the electronic structure on tunneling through ferroelectric insulators: Application to BaTiO ₃ and PbTiO ₃	3.2	17
12	Magnetoelectric effect in ferromagnetic-ferroelectric tunneling junctions. EPJ Applied Physics, 2011, 55, 30601.	0.7	0
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17	Electric field control of magnetism in multiferroic heterostructures. Journal of Physics Condensed Matter, 2012, 24, 333201.	1.8	342
18	Magneto-Electric Coupling in a Multiferroic Tunnel Junction Functioning as a Magnetic-Field-Effect Transistor. IEEE Nanotechnology Magazine, 2012, 11, 77-81.	2.0	4

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19	Tunneling magnetoresistance and electroresistance properties of composite barrier ferroelectric tunnel junctions. <i>Physica Status Solidi - Rapid Research Letters</i> , 2012, 6, 138-140.	2.4	3
20	Tunneling electroresistance effect in Pt/MgO/Pt/PbTiO ₃ /Pt ferroelectric tunnel junctions. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	8
21	Bias voltage effect on electron tunneling across a junction with a ferroelectric/ferromagnetic two-phase composite barrier. <i>Journal of Magnetism and Magnetic Materials</i> , 2012, 324, 1067-1070.	2.3	5
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23	A hybrid spin-charge mixed-mode simulation framework for evaluating STT-MRAM bit-cells utilizing multiferroic tunnel junctions. , 2013, , .		0
24	Polarization relaxation kinetics in ultrathin ferroelectric capacitors. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	23
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33	Improved memory functions in multiferroic tunnel junctions with a dielectric/ferroelectric composite barrier. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	19
34	Ca doping dependence of resistive switching characteristics in ferroelectric capacitors comprising Ca-doped BiFeO ₃ . <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	11
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42	Giant tunneling electroresistance in ferroelectric-gated silicene junction. <i>Journal of Magnetism and Magnetic Materials</i> , 2015, 374, 479-483.	2.3	2
43	Space-charge Effect on Electroresistance in Metal-Ferroelectric-Metal capacitors. <i>Scientific Reports</i> , 2016, 5, 18297.	3.3	30
44	Enhanced tunneling electroresistance in multiferroic tunnel junctions due to the reversible modulation of orbitals overlap. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	11
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